

Description

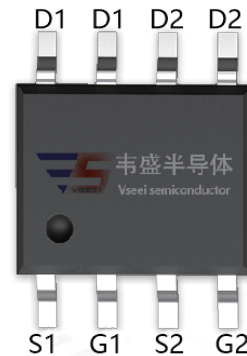
The VSM8DP03 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V.

General Features

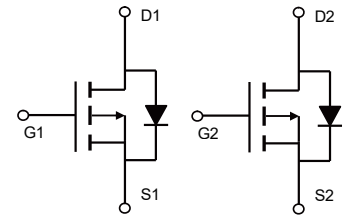
- $V_{DS} = -30V, I_D = -8A$
 $R_{DS(ON)} < 35m\Omega @ V_{GS} = -4.5V$
 $R_{DS(ON)} < 20m\Omega @ V_{GS} = -10V$
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- Battery Switch
- Load switch
- Power management



SOP-8



Schematic

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VSM8DP03	VSM8DP03-S8	SOP-8	Ø330mm	12mm	4000 units

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-8	A
Drain Current-Continuous ($T_C = 100^\circ\text{C}$)	$I_D (100^\circ\text{C})$	-5.7	A
Drain Current-Pulsed (Note 1)	I_{DM}	-32	A
Maximum Power Dissipation	P_D	3.1	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ\text{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	40	$^\circ\text{C/W}$
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Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-30	-33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1	-1.5	-3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-8A	-	16	20	mΩ
		V _{GS} =-4.5V, I _D =-8A	-	21	35	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-8A	10	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V, F=1.0MHz	-	1600	-	PF
Output Capacitance	C _{oss}		-	350	-	PF
Reverse Transfer Capacitance	C _{rss}		-	300	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-15V, I _D =-8A, V _{GS} =-10V, R _{GEN} =6Ω	-	10	-	nS
Turn-on Rise Time	t _r		-	15	-	nS
Turn-Off Delay Time	t _{d(off)}		-	110	-	nS
Turn-Off Fall Time	t _f		-	70	-	nS
Total Gate Charge	Q _g	V _{DS} =-15V, I _D =-8A, V _{GS} =-10V	-	30		nC
Total Gate Charge	Q _g	V _{DS} =-15V, I _D =-8A V _{GS} =-4.5V	-	17.8	-	
Gate-Source Charge	Q _{gs}		-	5.5	-	
Gate-Drain Charge	Q _{gd}		-	8	-	
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-8A	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

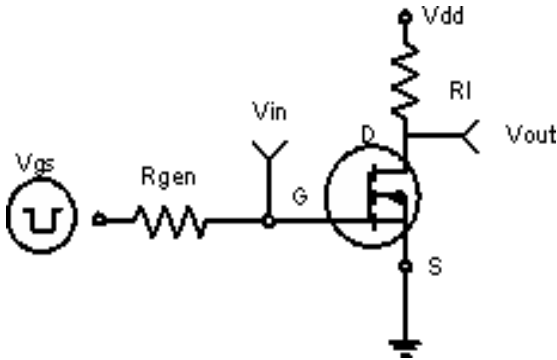


Figure 1: Switching Test Circuit

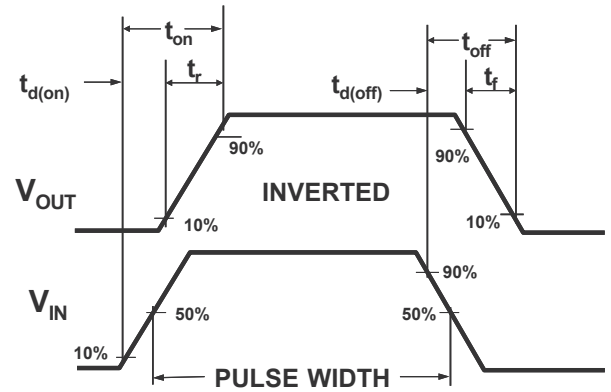


Figure 2: Switching Waveforms

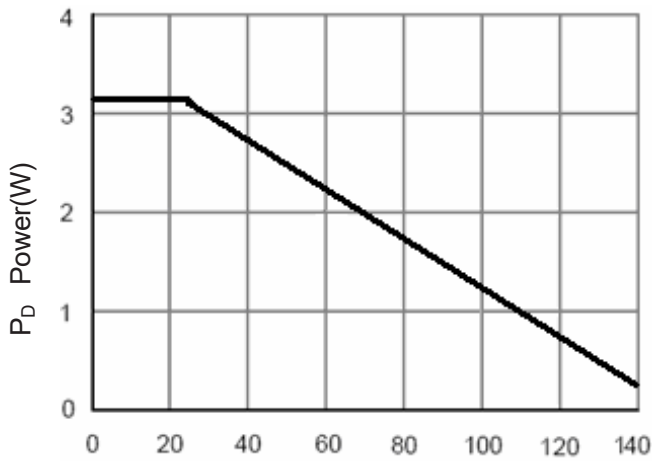


Figure 3 Power Dissipation

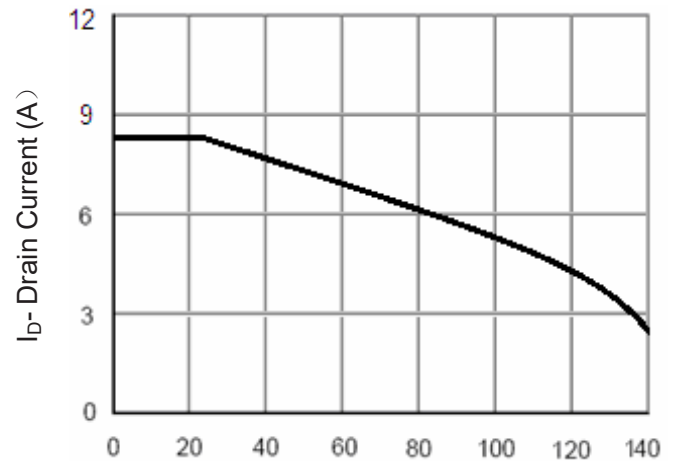


Figure 4 Drain Current

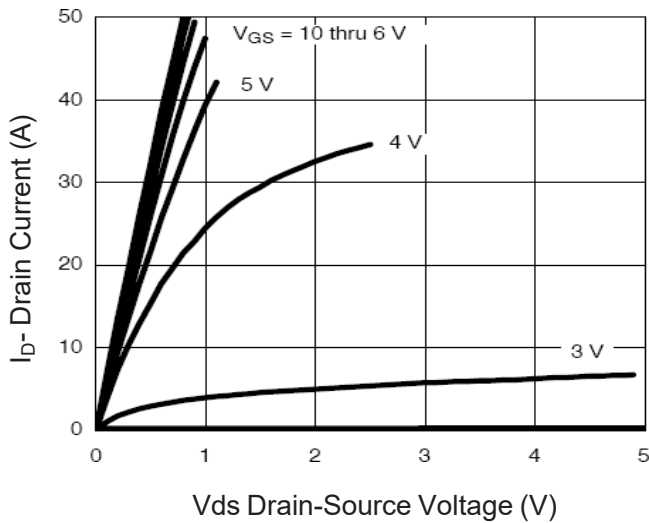


Figure 5 Output Characteristics

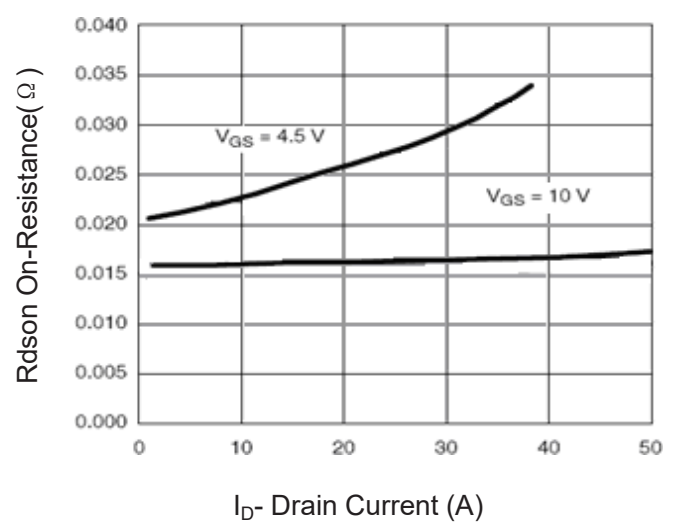
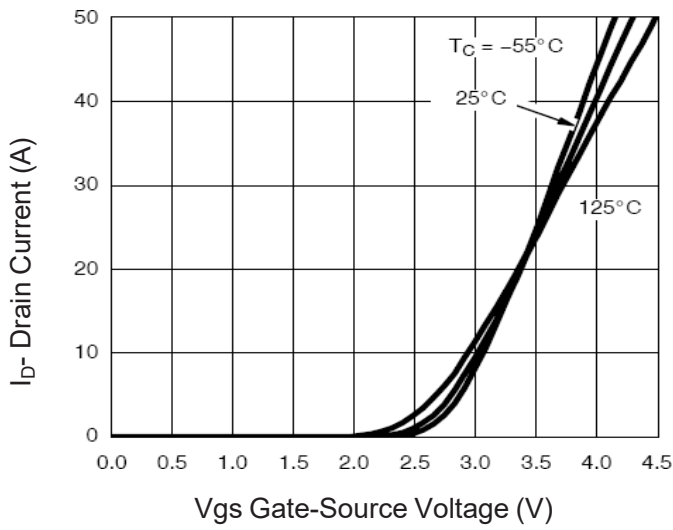
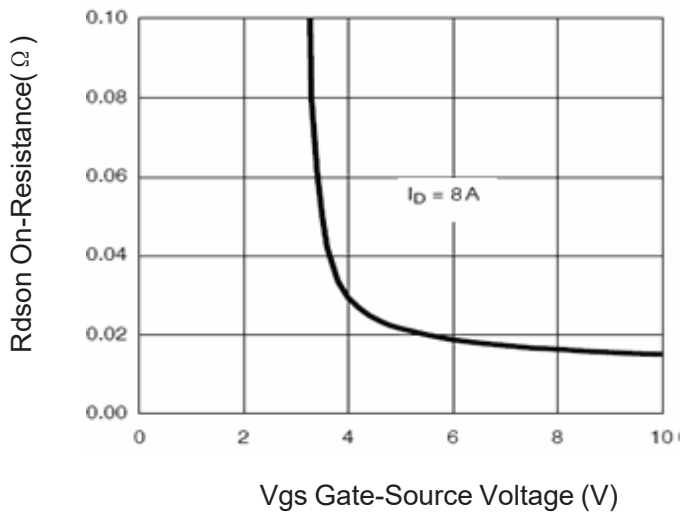
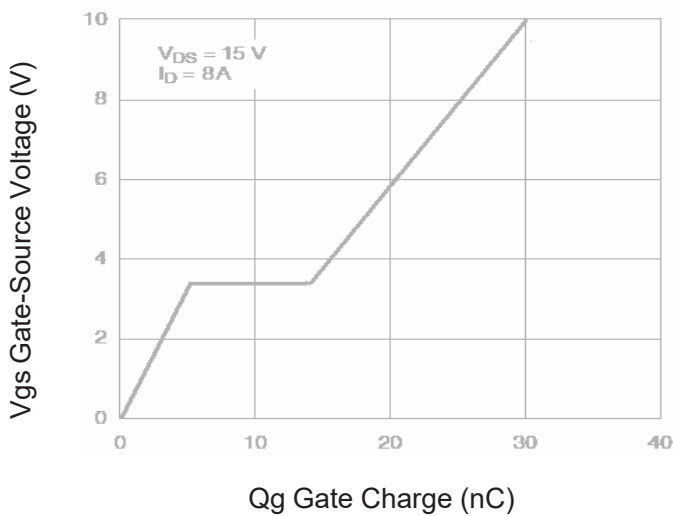
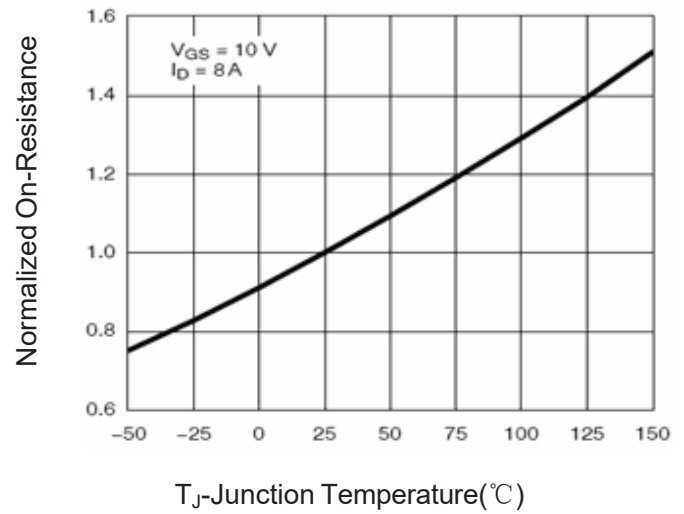
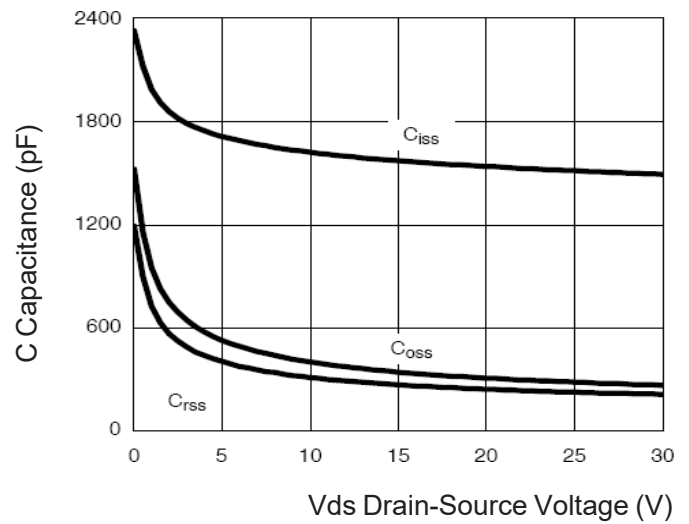
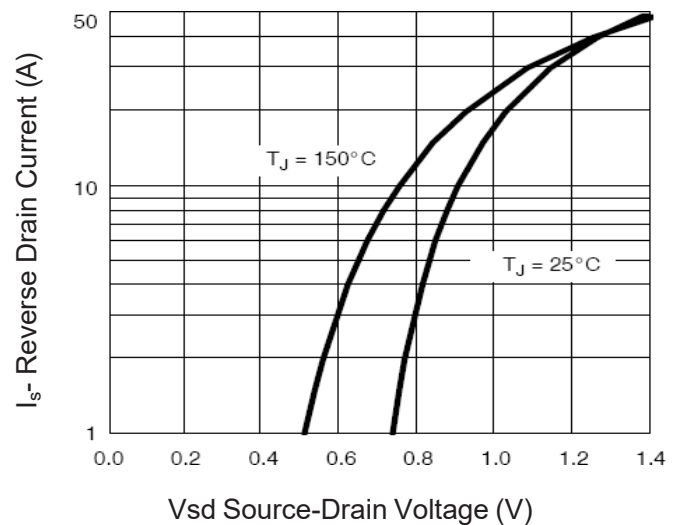


Figure 6 Drain-Source On-Resistance


Figure 7 Transfer Characteristics

Figure 9 Rdson vs Vgs

Figure 11 Gate Charge

Figure 8 Drain-Source On-Resistance

Figure 10 Capacitance vs Vds

Figure 12 Source- Drain Diode Forward

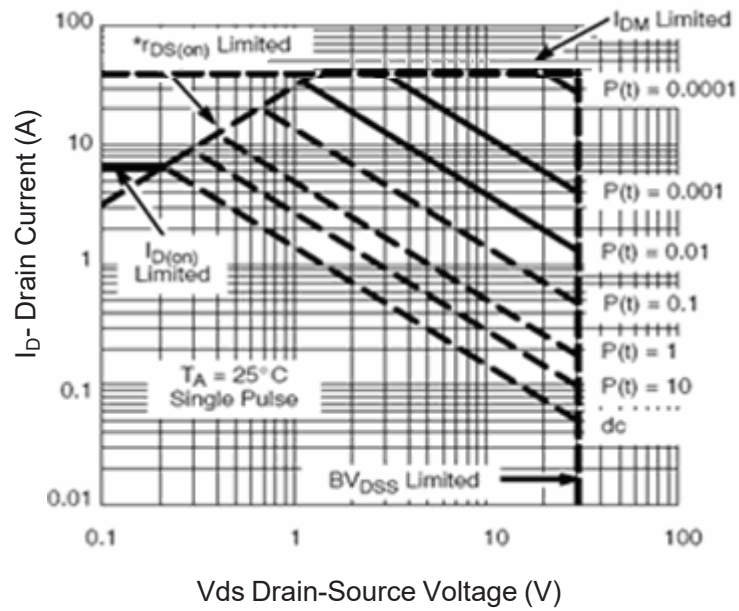


Figure 13 Safe Operation Area

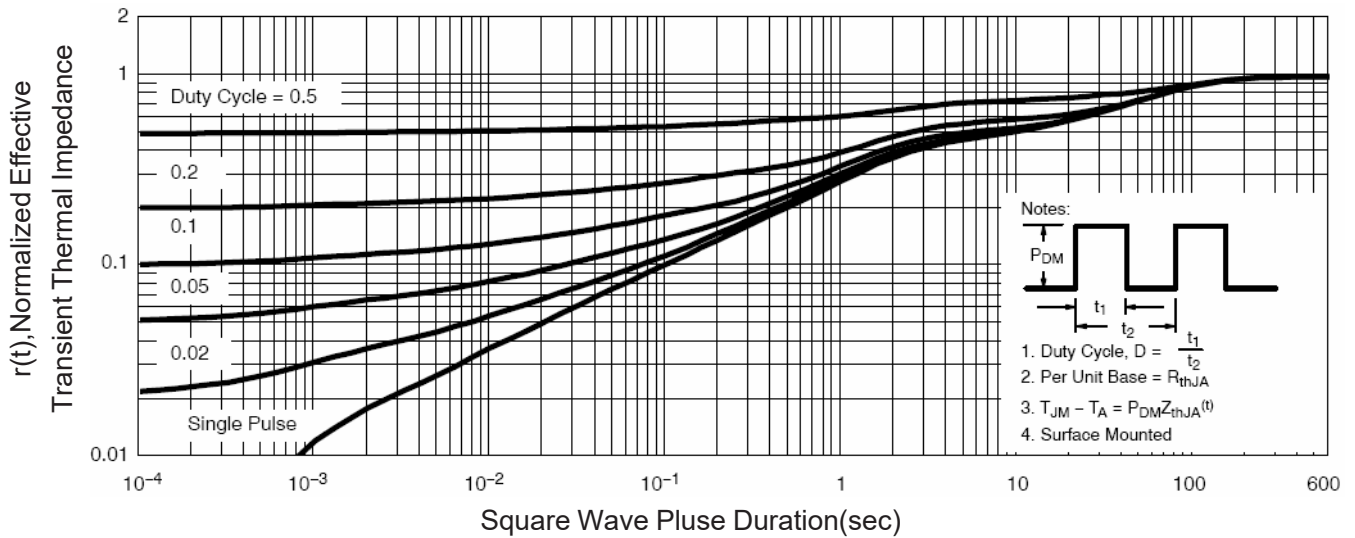


Figure 14 Normalized Maximum Transient Thermal Impedance